

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

1-23. (cancelled)

24. (currently amended) A method of concurrently forming two doped regions in a semiconductor substrate, comprising:

forming a mask layer over a semiconductor substrate;

patterning the mask layer to form two openings therein, wherein a first opening is larger than a second opening, ~~and wherein the first opening is larger than a second opening~~; and

selectively implanting the semiconductor substrate with ions through the openings in the patterned mask layer and diffusing the ions into the substrate, thereby defining a first implanted region associated with the first opening and having a first depth associated therewith and a second implanted region associated with the second opening and having a second depth associated therewith, and wherein the first depth is greater than the second depth.

25. (previously presented) The method of claim 24, wherein the mask layer comprises a photoresist.

26. (previously presented) The method of claim 24, wherein the semiconductor substrate is p-type and the ions are n-type.

27. (previously presented) The method of claim 24, wherein the total dopant in the first region is higher than the total dopant in the second region due to the first opening being larger than the design rule and the second opening being smaller than the design rule, and further comprising annealing the substrate, wherein the first region diffuses a distance which is greater than a diffusion distance of the second region, resulting in the first depth being greater than the second depth.